



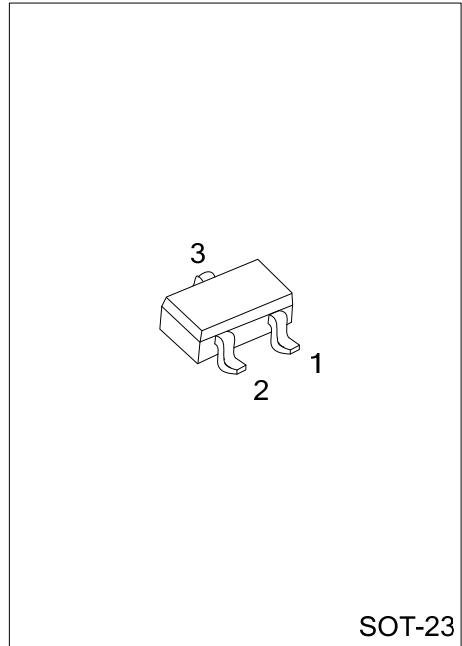
MMBTA06

NPN SILICON TRANSISTOR

AMPLIFIER TRANSISTOR

■ FEATURES

- * Collector-Emitter Voltage: $V_{CE0}=80V$
- * Collector Dissipation: $P_D=350mW$



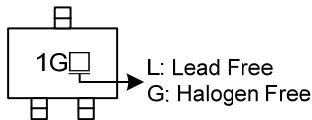
Lead-free: MMBTA06L
 Halogen-free: MMBTA06G

■ ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free	Halogen Free		1	2	3	
MMBTA06-AE3-R	MMBTA06L-AE3-R	MMBTA06G-AE3-R	SOT-23	E	B	C	Tape Reel

<p>MMBTA06L-AE3-R</p> <p>(1) Packing Type (2) Package Type (3) Lead Plating</p>	<p>(1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free, L: Lead Free, Blank: Pb/Sn</p>
---	---

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector Base Voltage	V _{CBO}	80	V
Collector Emitter Voltage	V _{CEO}	80	V
Emitter Base Voltage	V _{EBO}	4	V
Collector Current - Continuous	I _C	500	mA
Total Device Dissipation(Note 2)	P _D	350	mW
Derate Above 25°C		2.8	mW/°C
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Note 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Device mounted on FR-4=1.6×1.6×0.06 in

■ THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient	θ _{JA}		357		°C/W

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

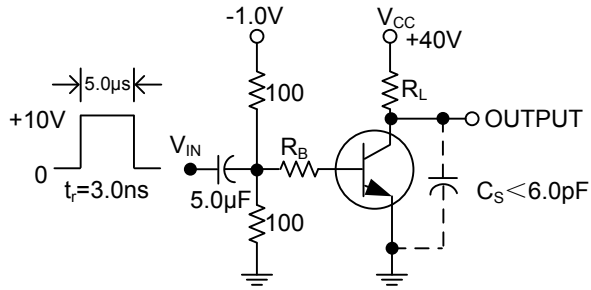
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector Emitter Breakdown Voltage (Note 1)	BV _{CEO}	I _C =1.0mA, I _B =0	80			V
Emitter Base Breakdown Voltage	BV _{EBO}	I _E =100μA, I _C =0	4			V
Collector Cutoff Current	I _{CES}	V _{CE} =60V, I _B =0			0.1	μA
Collector Cutoff Current	I _{CBO}	V _{CB} =80V, I _E =0			0.1	μA
ON CHARACTERISTICS						
DC Current Gain	h _{FE}	V _{CE} =1V, I _C =10mA,	100			
		V _{CE} =1V, I _C =100mA,	100			
Collector Emitter Saturation Voltage	V _{CE(SAT)}	I _C =100mA, I _B =10mA			0.25	V
Base Emitter on Voltage	V _{BE(ON)}	V _{CE} =1V, I _C =100mA,			1.2	V
SMALL-SIGNAL CHARACTERISTICS						
Current Gain Bandwidth Product (Note2)	f _T	V _{CE} =2V, I _C =10mA, f=100MHz	100			MHz

Note 1: Pulse test: PW≤300μs, Duty Cycle≤2%

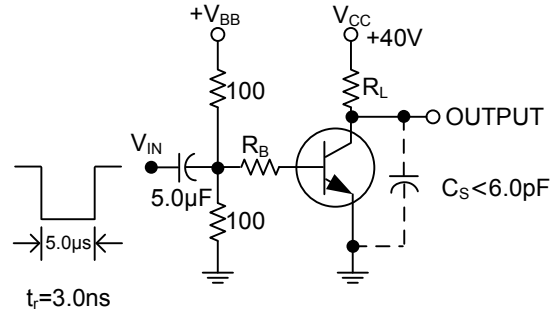
2: f_T is defined as the frequency at which I_{hfe} extrapolates to unity.

SWITCHING TIME TEST CIRCUITS

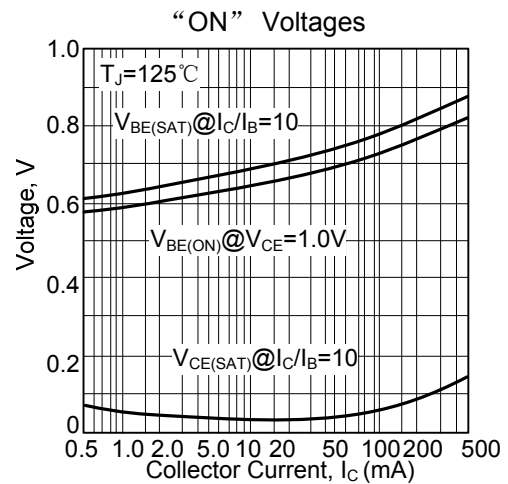
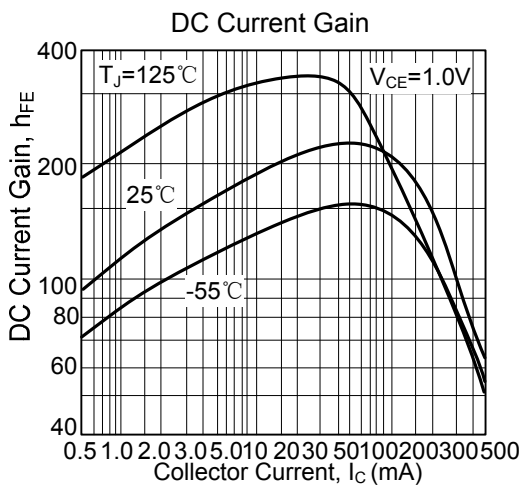
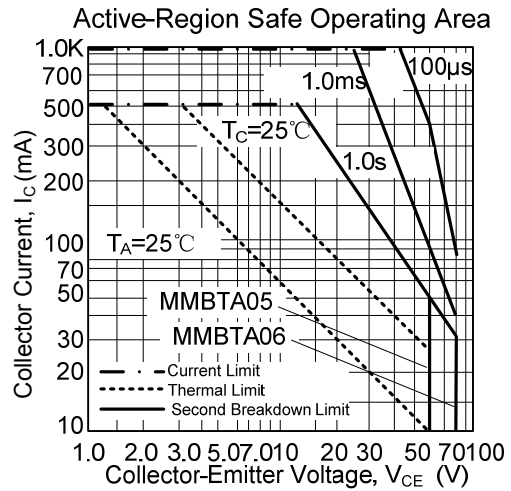
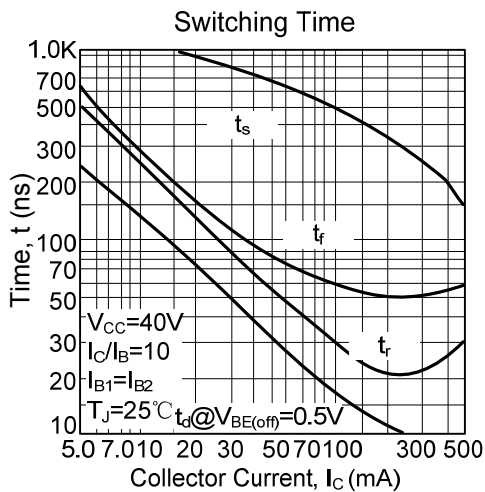
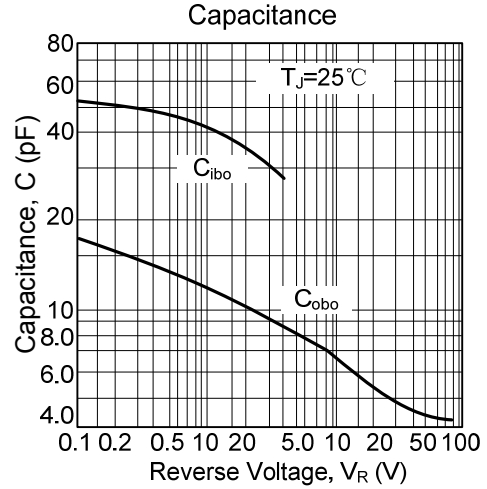
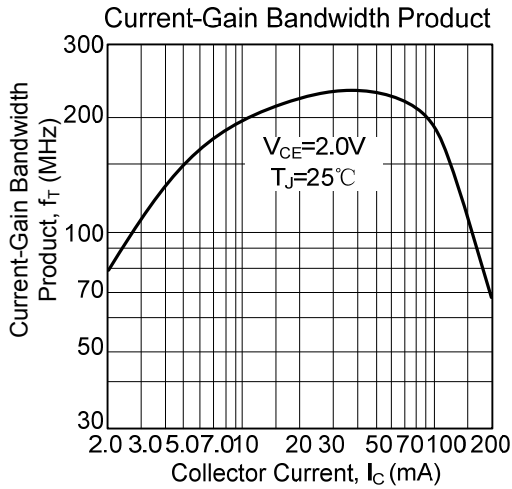
TURN-ON TIME



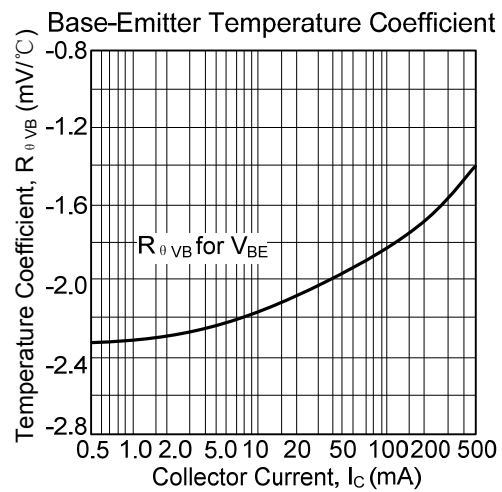
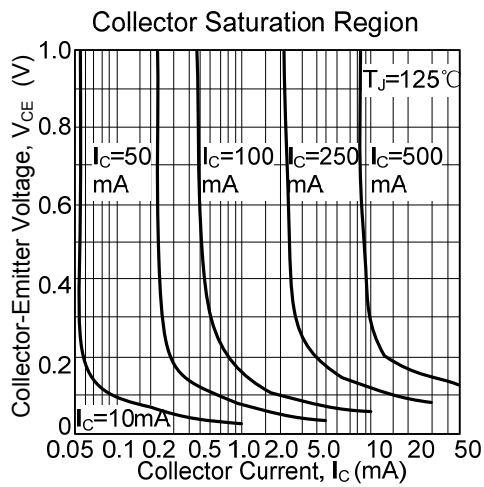
TURN-OFF TIME



TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.